

### Features

- Quadrant detector
- Low dark current
- Fast rise time, low capacitance
- High QE at 1064 nm
- Including heater and temperature sensor

### Description

Square active area quadrant PIN detector with 4 x 11 mm<sup>2</sup> active area and 70 μm gaps, optimized for 1064 nm. Metal can type hermetic, isolated TO package with ceramic heater and flat clear glass window.

### Application

- 1064 nm laser detection
- High speed photometry
- NIR pulsed light sensor

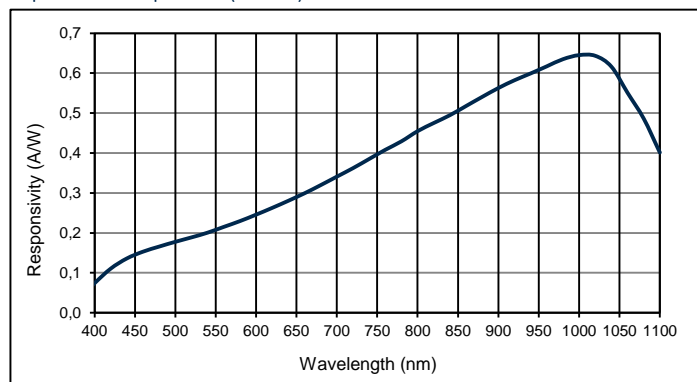
### RoHS

2011/65/EU

### Absolute maximum ratings

Symbol	Parameter	Min	Max	Unit
T <sub>STG</sub>	Storage temp	-55	125	°C
T <sub>OP</sub>	Operating temp	-40	85	°C
V <sub>OP</sub>	Operating voltage		250	V
I <sub>PEAK</sub>	Peak DC current		10	mA
p	Outside pressure		2	bar

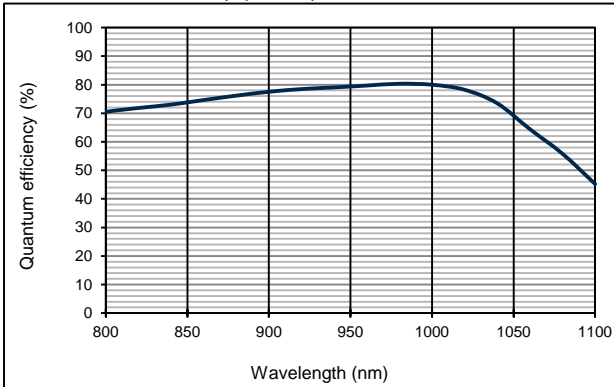
### Spectral response (23 °C)



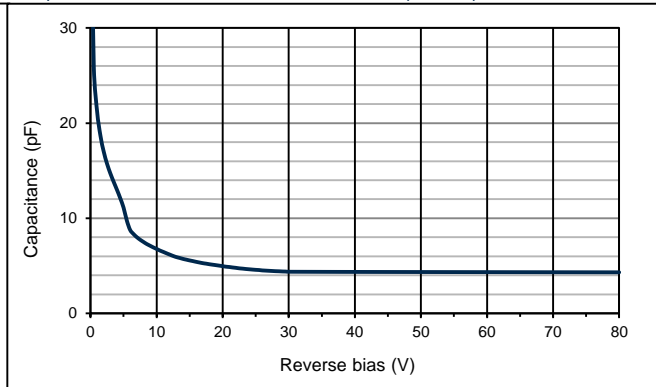
### Electro-optical characteristics @ 23 °C

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
	Active area	number of elements: 4 quadrants	6690 x 6690 (total)			μm
		per element	10.96			mm <sup>2</sup>
	Gap	between elements	70			μm
I <sub>D</sub>	Dark current	V <sub>R</sub> = 150 V, per element		8	15	nA
C	Capacitance	V <sub>R</sub> = 150 V, per element		5	6	pF
	Responsivity	V <sub>R</sub> = 150 V; λ = 1064 nm; R <sub>L</sub> = 50 Ω	0.42	0.48	0.65	A/W
t <sub>R</sub>	Rise time	V <sub>R</sub> = 180 V; λ = 1064 nm; R <sub>L</sub> = 50 Ω		10		ns
		180 V; 1064 nm; TIA terminated (R <sub>L</sub> = 1 Ω)		5.5		ns
V <sub>BR</sub>	Breakdown voltage	I <sub>R</sub> = 2 μA	250			V
	Temperature coefficient	Change of I <sub>PH</sub> with temperature		1.07		%/K
	Cross talk	V <sub>R</sub> = 150 V; λ = 1064 nm; R <sub>L</sub> = 50 Ω		0.5		%
	Heating time	23°C to 70°C with 21V power supply	1	2	3	s
	Heater resistance	23°C	36	40	44	Ω
	Temperature sensor	PTC, TK = 3500 ± 200 ppm/K	9950	10000	10050	Ω
	N.E.P.	V <sub>R</sub> = 150 V, λ = 1064 nm		1.1E-13		W/√Hz
FOV	Field of view		± 55			°

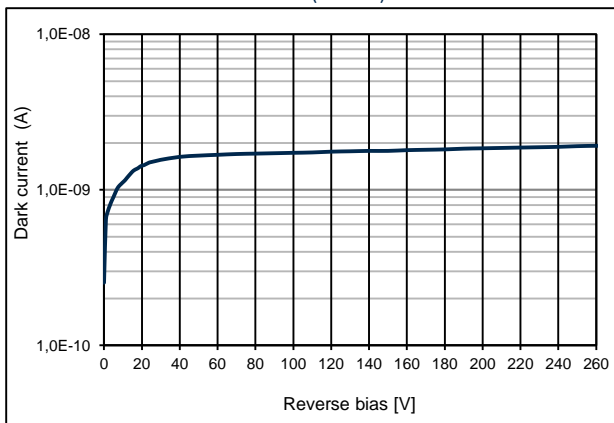
Quantum efficiency (23 °C)



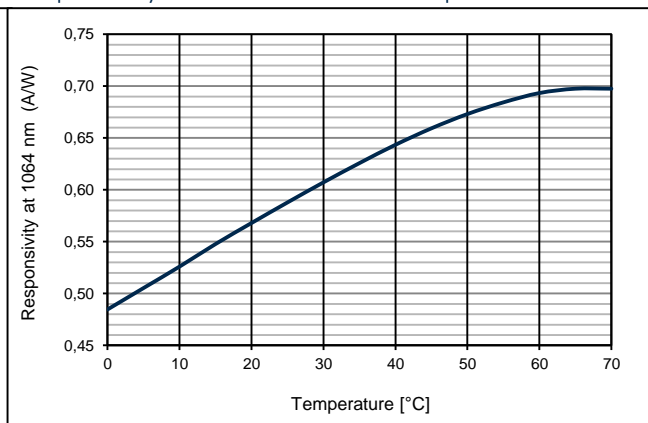
Capacitance as fct of reverse bias (23 °C)



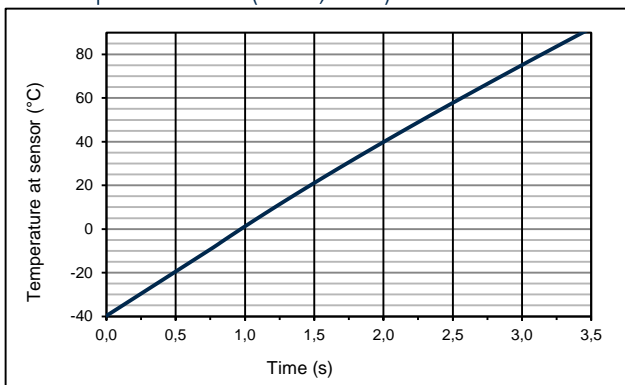
Dark current as fct of bias (23 °C)



Responsivity at 1064 nm as fct of temperature



Heater performance (23 °C, 21 V)



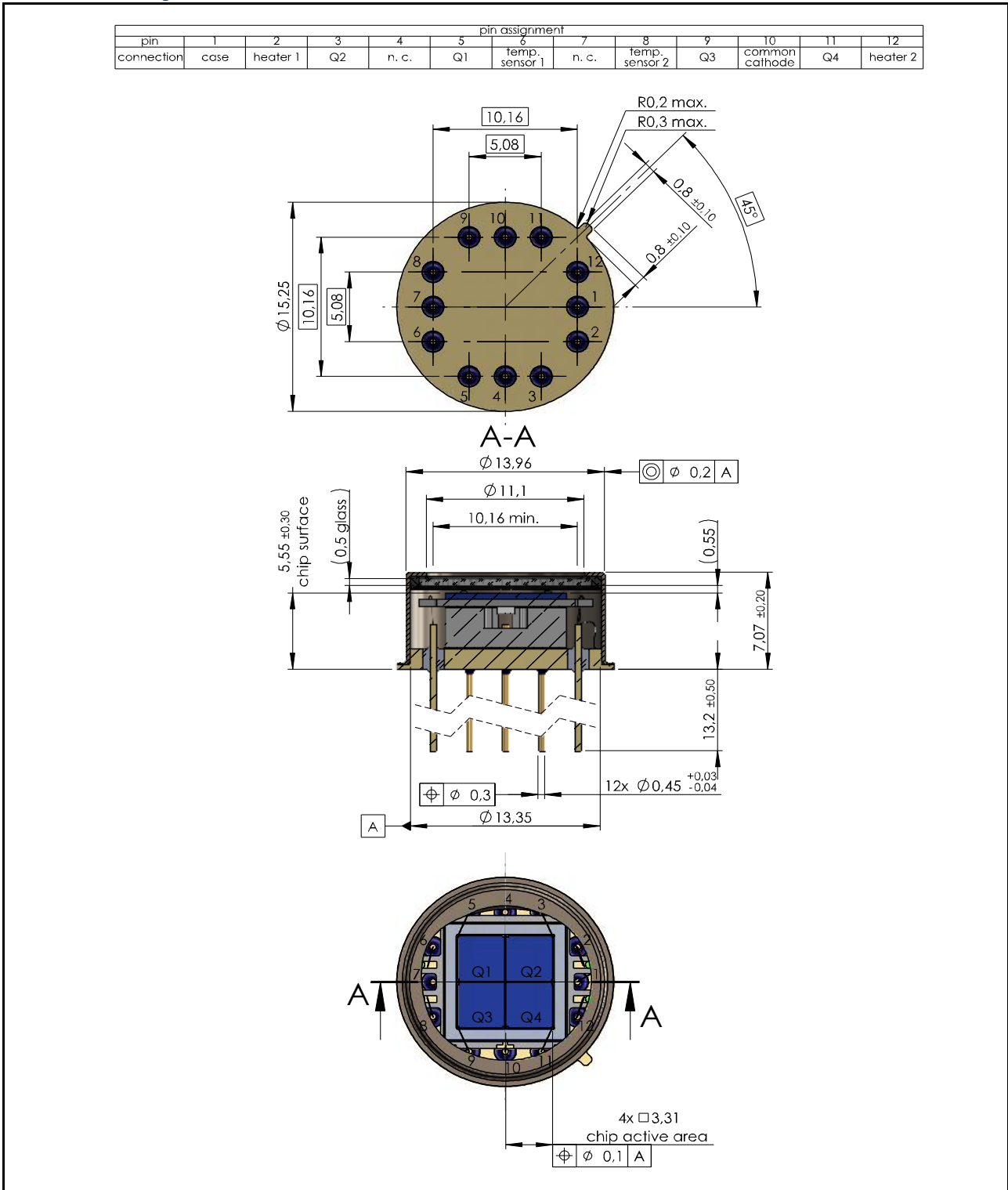
### Package dimension:

Small quantities: Foam pad, boxed (12 cm x 16.5 cm)

### Source of origin:

This detector and its components are manufactured in Germany.

## Technical Drawing



Disclaimer: Due to our strive for continuous improvement, specifications are subject to change within our PCN policy according to JESD46C.